

Low thermal conductivity in a new mixed metal telluride $\text{Mn}_{1.8(1)}\text{In}_{0.8(1)}\text{Si}_2\text{Te}_6$

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Electronic Supplementary Information (ESI)

Table S1: Important structural and refinement details of the $\text{Mn}_{1.78(5)}\text{In}_{0.84(2)}\text{Si}_2\text{Te}_6$ structure obtained from the Rietveld refinement of the PXRD data of the sample with the loaded composition of $\text{Mn}_{1.8}\text{In}_{0.8}\text{Si}_2\text{Te}_6$ ^a.

Refined composition	$\text{Mn}_{1.78(5)}\text{In}_{0.84(2)}\text{Si}_2\text{Te}_6$
Space group	$P\bar{3}1m$
a (Å)	7.0370(2)
c (Å)	7.1131(2)
V (Å ³)	305.04(3)
Z	2
ρ (g cm ⁻³)	5.51
GOF on F^2	1.98
bR_p	5.54
$^cR_{wp}$	8.34

^a $\lambda = 1.5406$ Å, $T = 298(2)$ K.

$$^bR_p = \sum |Y_{o,m} - Y_{c,m}| / \sum Y_{o,m}$$

$$^cR_{wp} = \{\sum [w_m(Y_{o,m} - Y_{c,m})^2] / \sum w_m Y_{o,m}^2\}^{1/2} \text{ For } w_m = 1/\sigma(Y_{o,m})^2$$

Table S2: Fractional atomic coordinates and site occupancy factors (SOF) obtained from the Rietveld refinement of the $\text{Mn}_{1.78(5)}\text{In}_{0.84(2)}\text{Si}_2\text{Te}_6$ structure using the PXRD data.

Atoms	Wyckoff Position	Site Symmetry	x	y	z	SOF
In1	$2d$	$3\cdot 2$	$1/3$	$2/3$	0	0.42(2)
Mn1	$2d$	$3\cdot 2$	$1/3$	$2/3$	0	0.58(2)
Mn2	$2c$	$3\cdot 2$	$1/3$	$2/3$	$1/2$	0.31(5)
Si1	$2e$	$3\cdot m$	0	0	0.1630(5)	1
Te1	$6k$	$\cdot\cdot m$	0.3422(5)	0	0.2602(5)	1

Table S3 Atomic displacement parameters ($\text{\AA}^2$) for the $\text{Mn}_{1.8(1)}\text{In}_{0.8(1)}\text{Si}_2\text{Te}_6$ structure obtained from the SCXRD study.

	U^{11}	U^{22}	U^{33}	U^{12}	U^{13}	U^{23}
$\text{Mn}_{1.8(1)}\text{In}_{0.8(1)}\text{Si}_2\text{Te}_6$						
In1	0.0238(7)	0.0238(7)	0.0512(15)	0.0119(4)	0.000	0.000
Mn1	0.0238(7)	0.0238(7)	0.0512(15)	0.0119(4)	0.000	0.000
Mn2	0.032(5)	0.032(5)	0.018(6)	0.016(2)	0.000	0.000
Si1	0.0130(14)	0.0130(14)	0.030(3)	0.0065(7)	0.000	0.000
Te1	0.0143(3)	0.0187(4)	0.0272(4)	0.00934(19)	-0.0017(3)	0.000

Table S4 All the bond angles (in degrees) in the $\text{Mn}_{1.8(1)}\text{In}_{0.8(1)}\text{Si}_2\text{Te}_6$ structure obtained from the SCXRD study.

Te1i—In1—Te1ii	96.17 (3)	Te1viii—Mn2—Te1ix	88.382 (18)
Te1i—In1—Te1iii	85.181 (17)	Te1ii—Mn2—Te1ix	177.97 (2)

Telii—In1—Teliii	93.502 (19)	Teliv—Mn2—Telvi	88.382 (18)
Teli—In1—Teliv	93.502 (19)	Telvii—Mn2—Telvi	93.05 (3)
Telii—In1—Teliv	85.181 (17)	Telviii—Mn2—Telvi	177.97 (2)
Teliii—In1—Teliv	178.03 (2)	Telii—Mn2—Telvi	88.382 (18)
Teli—In1—Telv	85.181 (17)	Telix—Mn2—Telvi	90.22 (2)
Telii—In1—Telv	178.03 (2)	Si1x—Si1—Tel	106.10 (14)
Teliii—In1—Telv	85.181 (17)	Si1x—Si1—Telxi	106.10 (14)
Teliv—In1—Telv	96.17 (3)	Tel—Si1—Telxi	112.62 (12)
Teli—In1—Telvi	178.03 (2)	Si1x—Si1—Teliv	106.10 (14)
Telii—In1—Telvi	85.181 (17)	Tel—Si1—Teliv	112.62 (12)
Teliii—In1—Telvi	96.17 (3)	Telxi—Si1—Teliv	112.62 (12)
Teliv—In1—Telvi	85.181 (17)	Si1—Tel—Mn2vii	122.44 (8)
Telv—In1—Telvi	93.502 (19)	Si1—Tel—Mn2xii	122.44 (8)
Teliv—Mn2—Telvii	177.97 (2)	Mn2vii—Tel—Mn2xii	89.78 (2)
Teliv—Mn2—Telviii	90.22 (2)	Si1—Tel—In1iii	100.84 (10)
Telvii—Mn2—Telviii	88.382 (18)	Mn2vii—Tel—In1iii	75.007 (12)
Teliv—Mn2—Telii	88.382 (18)	Mn2xii—Tel—In1iii	135.10 (3)
Telvii—Mn2—Telii	90.22 (2)	Si1—Tel—In1xii	100.84 (10)
Telviii—Mn2—Telii	93.05 (3)	Mn2vii—Tel—In1xii	135.10 (3)
Teliv—Mn2—Telix	93.05 (3)	Mn2xii—Tel—In1xii	75.007 (12)
Telvii—Mn2—Telix	88.382 (18)	In1iii—Tel—In1xii	86.50 (2)

Symmetry codes: (i) $y, -x+y+1, -z$; (ii) $x, y+1, z$; (iii) $-x+1, -y+1, -z$; (iv) $-y, x-y, z$; (v) $x-y, x, -z$; (vi) $-x+y+1, -x+1, z$; (vii) $-x+1, -y+1, -z+1$; (viii) $y, -x+y+1, -z+1$; (ix) $x-y, x, -z+1$; (x) $-x, -y, -z$; (xi) $-x+y, -x, z$; (xii) $x, y-1, z$.

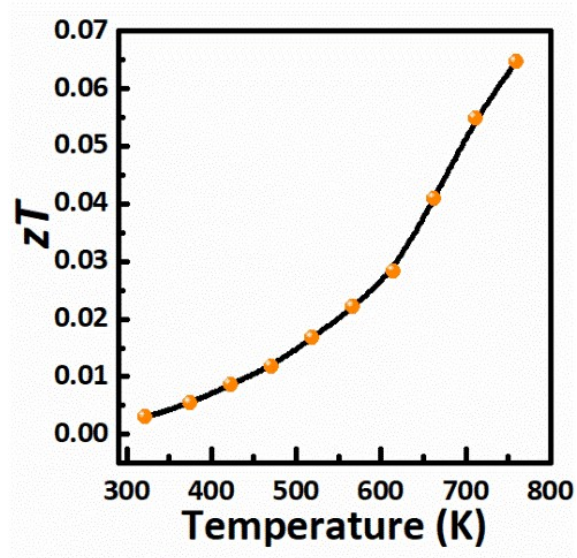


Fig. S1: The thermoelectric figure of merit (zT) of the polycrystalline sample $\text{Mn}_{1.8}\text{In}_{0.8}\text{Si}_2\text{Te}_6$. Each data point has an estimated error of 20%.